rmivas	institute	of	Tecanoid	

10EE764

USN

Seventh Semester B.E. Degree Examination, Feb./Mar.2022 **VLSI Circuits and Design**

Max. Marks:100 Time: 3 hrs.

No	ote:	Answer any FIVE full questions, selecting at least TWO questions from e	ach part.
		PART-A	(10.3/1)
1	a.	Explain the fabrication steps of P-well CMOS process.	(10 Marks)
	b.	Explain the transistor action of enhancement mode nMOS transistor for differen	
		V_{gs} and V_{ds} .	(06 Marks)
	C.	Compare CMOS and BJT technologies.	(04 Marks)
_			:
2	a.	Derive an expression for the drain current I _{ds} of an enhancement mode nMOS tr	ansistor for
		the following regions:	
		(i) Linear (ii) Saturation. (iii) Cutoff.	(10 3/
		Also plot I_{ds} , V_s V_{ds} and mark the above regions.	(10 Marks)
	b.	Explain the five regions of operations of CMOS inverter transfer characteristics.	(10 Marks)
_		De la circle de la companya de la co	Evaloin
3	a.	Draw the circuit diagram of a 2-input CMOS NAND gate along with stick diagram	
		the working of the circuit.	(08 Marks)
	b.	Indicate and draw design rule for diffusion layers and metal layers.	(06 Marks) (06 Marks)
	C.	Distinguish buried and butting contacts with suitable diagrams.	(00 Marks)
4		Explain the terms: (i) Rise time (ii) Full time. Derive the equations for the r	ise time (t.)
4	a.	and fall time (t_f) of CMOS inverter. Also derive the conditions for $t_r = t_f$.	(10 Marks)
	b.	Derive the expression for total delay for N stages of nMOS and CMOS inverters	
	υ.	width factor f and delay T.	(06 Marks)
	0	Write a short note on choice of layers.	(04 Marks)
	c.	Write a short note on choice of layers.	(01111111)
		PART – B	
5	a.	Obtain the scaling factor for the following parameters:	
3	u.	(i) Gate Capacitance (Cg)	
		(ii) Current Density (J)	
		(iii) Maximum Operating Frequency (f ₀)	
		(iv) Power speed product (P_T)	
		(v) Gate delay (T_d)	(10 Marks)
	b.	Discuss the limitation of scaling on substrate doping and depletion width.	(10 Marks)
6	a.	Explain the working of switch logic, pass-transistor and transmission gates with	their merits
		and demerits.	(10 Marks)
	b.	Explain the structural design concept using bus arbitration logic as an example.	(10 Marks)
		-	

- What are the general considerations to be followed in designing a subsystem? (08 Marks) 7
- a. What are the basic requirements of a shifter? Explain with an example of 4×4 cross bar b. switch. What are the drawbacks of this basic switch and how is it overcome? (12 Marks)
- Design a 4-bit adder and then show how it can be used to implement the ALU functions. 8 a. (12 Marks)
 - Explain the arrangement of a 4-bit serial-parallel multiplier. (08 Marks)

2. Any revealing of identification, appeal to evaluator and l or equations written eg, 42+8=50, will be treated as malpractice. Important Note: 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.